# **BLC9H10XS-505A**

## **Power LDMOS transistor**

**AMPLEON** 

Rev. 1 — 6 March 2020

Product data sheet

### 1. Product profile

#### 1.1 General description

500 W LDMOS packaged asymmetric Doherty power transistor for base station applications at frequencies from 617 MHz to 960 MHz.

#### Table 1. Typical performance 800 MHz

Typical RF performance at  $T_{\rm case}$  = 25 °C in an asymmetrical Doherty test circuit.  $V_{\rm DS}$  = 48 V;  $I_{\rm Dq}$  = 500 mA (main);  $V_{\rm GS(amp)peak}$  = 0.5 V; unless otherwise specified.

| Test signal      | f          | V <sub>DS</sub> | P <sub>L(AV)</sub> | G <sub>p</sub> | η <sub>D</sub> | ACPR               |
|------------------|------------|-----------------|--------------------|----------------|----------------|--------------------|
|                  | (MHz)      | (V)             | (dBm)              | (dB)           | (%)            | (dBc)              |
| 1-carrier W-CDMA | 791 to 821 | 48              | 49.3               | 18.6           | 52             | -36 <sup>[1]</sup> |

Test signal: 1-carrier W-CDMA; 3GPP test model 1; 64 DPCH; PAR = 9.6 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internal integrated wideband input matching for ease of use
- Integrated ESD protection
- For RoHS compliance see the product details on the Ampleon website

#### 1.3 Applications

RF power amplifiers for base stations and multi carrier applications in the 617 MHz to 960 MHz frequency range

### 2. Pinning information

Table 2. Pinning

| Pin | Description | S   | implified o | utline | Graphic symbol |
|-----|-------------|-----|-------------|--------|----------------|
| 1   | drain1      |     | -~-         | ~      |                |
| 2   | drain2      |     | 1           | 2      | اً             |
| 3   | gate1       | 1   | ( )         | , ,    | <u>•</u>       |
| 4   | gate2       |     |             |        | 5              |
| 5   | source      | [1] |             |        | 4              |
|     |             | "   | 3           | 4      | 2<br>sym117    |

[1] Connected to flange.

### 3. Ordering information

Table 3. Ordering information

| Type number    | Packag | Package   |           |  |  |
|----------------|--------|---|-----------|--|--|
|                | Name   | Description   | Version   |  |  |
| BLC9H10XS-505A | -      | air cavity plastic earless flanged package; 4 leads | SOT1273-1 |  |  |

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol                   | Parameter                          | Conditions    | Min | Max  | Unit |
|--------------------------|------------------------------------|---------------|-----|------|------|
| $V_{DS}$                 | drain-source voltage               |               | -   | 110  | V    |
| V <sub>GS(amp)main</sub> | main amplifier gate-source voltage |               | -6  | +11  | V    |
| V <sub>GS(amp)peak</sub> | peak amplifier gate-source voltage |               | -6  | +11  | V    |
| T <sub>stg</sub>         | storage temperature                |               | -65 | +150 | °C   |
| Tj                       | junction temperature               | [1]           | -   | 225  | °C   |
| T <sub>case</sub>        | case temperature                   | operating [1] | -40 | +150 | °C   |

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator

#### 5. Thermal characteristics

Table 5. Thermal characteristics

| Symbol               | Parameter                                | Conditions   | Тур   | Unit |
|----------------------|--|--|-------|------|
| R <sub>th(j-c)</sub> | thermal resistance from junction to case | $V_{DS} = 48 \text{ V; } I_{Dq} = 500 \text{ mA;}$<br>$V_{GS(peak)} = 0.65 \text{ V; } T_{case} = 80 ^{\circ}\text{C}$ |       |      |
|                      |  | P <sub>L</sub> = 81 W  | 0.346 | K/W  |
|                      |  | P <sub>L</sub> = 100 W   | 0.327 | K/W  |

#### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

| Symbol               | Parameter                        | Conditions   | Min | Тур      | Max | Unit |
|----------------------|----------------------------------|--|-----|----------|-----|------|
| Main dev             | rice                             |  |     | <b>-</b> |     |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown voltage   | $V_{GS} = 0 \text{ V}; I_D = 1.5 \text{ mA}$                       | 108 | -        | -   | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | $V_{DS} = 10 \text{ V}; I_D = 150 \text{ mA}$                      | 1.5 | 2.0      | 2.5 | V    |
| $V_{GSq}$            | gate-source quiescent voltage    | $V_{DS} = 48 \text{ V}; I_D = 500 \text{ mA}$                      | 1.7 | 2.0      | 2.7 | V    |
| I <sub>DSS</sub>     | drain leakage current            | $V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$                      | -   | -        | 1.4 | μΑ   |
| I <sub>DSX</sub>     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$<br>$V_{DS} = 10 \text{ V}$ | -   | 24.3     | -   | A    |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V                      | -   | -        | 140 | nA   |
| g <sub>fs</sub>      | forward transconductance         | $V_{DS} = 10 \text{ V}; I_D = 7.5 \text{ A}$                       | -   | 10       | -   | S    |
| R <sub>DS(on)</sub>  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$<br>$I_D = 5.25 \text{ A}$  | -   | 154      | 203 | mΩ   |
| Peak dev             | vice                             | 1  |     | 1        |     |      |
| V <sub>(BR)DSS</sub> | drain-source breakdown voltage   | $V_{GS} = 0 \text{ V}; I_D = 2.2 \text{ mA}$                       | 108 | -        | -   | V    |
| V <sub>GS(th)</sub>  | gate-source threshold voltage    | $V_{DS} = 10 \text{ V}; I_D = 220 \text{ mA}$                      | 1.5 | 2.0      | 2.5 | V    |
| $V_{GSq}$            | gate-source quiescent voltage    | $V_{DS} = 48 \text{ V}; I_D = 800 \text{ mA}$                      | 1.7 | 2.0      | 2.7 | V    |
| I <sub>DSS</sub>     | drain leakage current            | V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V                      | -   | -        | 1.4 | μΑ   |
| I <sub>DSX</sub>     | drain cut-off current            | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$<br>$V_{DS} = 10 \text{ V}$ | -   | 35.5     | -   | A    |
| I <sub>GSS</sub>     | gate leakage current             | V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V                      | -   | -        | 140 | nA   |
| 9 <sub>fs</sub>      | forward transconductance         | V <sub>DS</sub> = 10 V; I <sub>D</sub> = 11 A                      | -   | 14.0     | -   | S    |
| R <sub>DS(on)</sub>  | drain-source on-state resistance | $V_{GS} = V_{GS(th)} + 3.75 \text{ V};$<br>$I_D = 7.7 \text{ A}$   | -   | 113      | 142 | mΩ   |

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 - 64 DPCH;  $f_1$  = 793.5 MHz;  $f_2$  = 818.5 MHz; RF performance at  $V_{DS}$  = 48 V;  $I_{Dq}$  = 400 mA (main);  $V_{GS(amp)peak}$  = 0.5 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 791 MHz to 821 MHz.

| Symbol     | Parameter                    | Conditions                | Min  | Тур  | Max | Unit |
|------------|------------------------------|---------------------------|------|------|-----|------|
| Gp         | power gain                   | P <sub>L(AV)</sub> = 85 W | 16.8 | 18.2 | -   | dB   |
| RLin       | input return loss            | P <sub>L(AV)</sub> = 85 W | -    | -17  | -13 | dB   |
| $\eta_{D}$ | drain efficiency             | P <sub>L(AV)</sub> = 85 W | 46   | 50   | -   | %    |
| ACPR       | adjacent channel power ratio | P <sub>L(AV)</sub> = 85 W | -    | -33  | -28 | dBc  |

#### Table 8. RF characteristics

Test signal: CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %;  $f_1$  = 791 MHz;  $f_2$  = 821 MHz; RF performance at  $V_{DS}$  = 48 V;  $I_{Dq}$  = 400 mA;  $V_{GS(amp)peak}$  = 0.6 V (typical);  $T_{case}$  = 25 °C; unless otherwise specified; in a Doherty production RF test circuit.

| Symbol              | Parameter                        | Conditions | Min | Тур | Max | Unit |
|---------------------|----------------------------------|------------|-----|-----|-----|------|
| P <sub>L(3dB)</sub> | output power at 3 dB compression | -          | 485 | 500 | -   | W    |

#### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC9H10XS-505A is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 48 V;  $I_{Dq}$  = 400 mA;  $V_{GS(amp)peak}$  = 0.6 V; f = 791 MHz;  $P_L$  = 160 W (5 dB OBO); W-CDMA.

#### 7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq} = 900$  mA (main);  $V_{DS} = 48$  V; pulsed CW ( $t_p = 100 \ \mu s$ ;  $\delta = 10 \ \%$ ).

| f       | Z <sub>S</sub> [1]  | Z <sub>L</sub> [1]  | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |
|---------|---------------------|---------------------|--------------------|--------------------|--------------------|
| (MHz)   | <b>(</b> Ω <b>)</b> | <b>(</b> Ω <b>)</b> | (W)                | (%)                | (dB)               |
| Maximum | power load          |                     |                    |                    |                    |
| 780     | 3.8 – j3.4          | 1.5 – j0.3          | 330                | 65.0               | 19.3               |
| 820     | 4.2 – j4.2          | 1.7 – j0.5          | 337                | 66.4               | 19.1               |
| 860     | 4.9 – j4.9          | 1.6 – j0.7          | 334                | 65.2               | 18.8               |
| Maximum | n drain efficiency  | load                |                    |                    |                    |
| 780     | 3.8 – j3.4          | 1.5 + j1.0          | 198                | 74.6               | 22.2               |
| 820     | 4.2 – j4.2          | 1.3 + j0.6          | 231                | 75.7               | 21.2               |
| 860     | 4.9 – j4.9          | 1.3 + j0.4          | 230                | 75.9               | 21.2               |

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

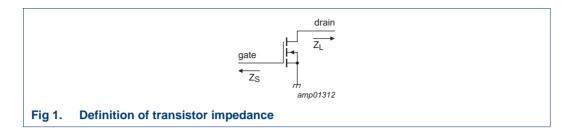
Measured load-pull data of peak device;  $I_{Dq} = 1320$  mA (peak);  $V_{DS} = 48$  V; pulsed CW ( $t_p = 100 \ \mu s$ ;  $\delta = 10 \ \%$ ).

| f       | Z <sub>S</sub> [1]  | Z <sub>L</sub> [1]  | P <sub>L</sub> [2] | η <sub>D</sub> [2] | G <sub>p</sub> [2] |
|---------|---------------------|---------------------|--------------------|--------------------|--------------------|
| (MHz)   | <b>(</b> Ω <b>)</b> | <b>(</b> Ω <b>)</b> | (W)                | (%)                | (dB)               |
| Maximum | power load          |                     |                    |                    |                    |
| 780     | 3.1 – j2.1          | 1.3 – j1.0          | 451                | 62.4               | 18.4               |
| 820     | 4.0 – j3.4          | 1.2 – j0.9          | 451                | 65.6               | 18.4               |
| 860     | 4.7 – j3.5          | 1.1 – j1.0          | 458                | 67.3               | 18.3               |
| Maximum | drain efficiency    | load                |                    |                    |                    |
| 780     | 3.1 – j2.1          | 1.1 + j0.0          | 324                | 72.4               | 20.9               |
| 820     | 4.0 – j3.4          | 0.9 – j0.2          | 343                | 72.9               | 20.1               |
| 860     | 4.7 – j3.5          | 0.9 – j0.2          | 319                | 77.4               | 20.9               |

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in <u>Figure 1</u>.

<sup>[2]</sup> At 3 dB gain compression.

<sup>[2]</sup> At 3 dB gain compression.



#### 7.3 Test circuit

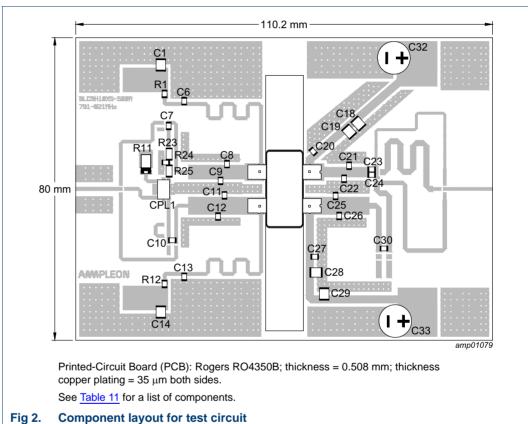


Table 11. List of components See Figure 2 for component layout.

|                               | ,                                 |               |  |
|-------------------------------|-----------------------------------|---------------|--|
| Component                     | Description                       | Value         | Remarks                                      |
| C1, C14                       | multilayer ceramic chip capacitor | 4.7 μF, 50 V  | Murata: GRM32ER71H475KA88L, SMD 1210         |
| C18, C19, C28, C29            | multilayer ceramic chip capacitor | 4.7 μF, 100 V | Murata: GRM42-256X7S475K100H530,<br>SMD 1210 |
| C6, C7, C10, C13,<br>C27, C30 | multilayer ceramic chip capacitor | 68 pF         | Murata: Hi-Q, SMD 0805                       |
| C8, C9                        | multilayer ceramic chip capacitor | 3.9 pF        | Murata: Hi-Q, SMD 0805                       |
| C11, C12                      | multilayer ceramic chip capacitor | 5.6 pF        | Murata: Hi-Q, SMD 0805                       |
| C20                           | multilayer ceramic chip capacitor | 39 pF         | Murata: Hi-Q, SMD 0805                       |
| C21, C22                      | multilayer ceramic chip capacitor | 8.2 pF        | ATC 100B                                     |
| C23, C24                      | multilayer ceramic chip capacitor | 10 pF         | Murata: Hi-Q, SMD 0805                       |

BLC9H10XS-505A

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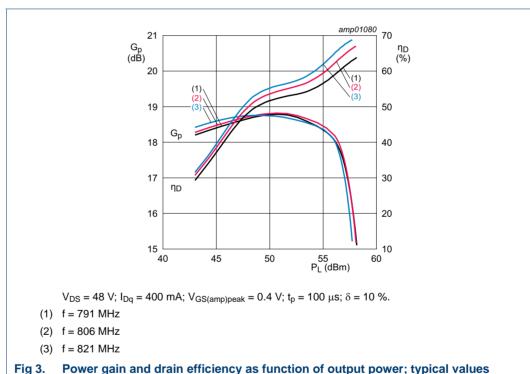
Table 11. List of components ... continued

See Figure 2 for component layout.

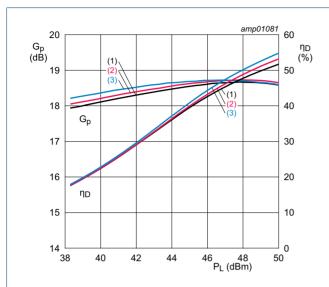
| Component | Description                       | Value          | Remarks             |
|-----------|-----------------------------------|----------------|---------------------|
| C25       | multilayer ceramic chip capacitor | 12 pF          | ATC 800B            |
| C26       | multilayer ceramic chip capacitor | 10 pF          | ATC 800B            |
| C32, C33  | electrolytic capacitor            | 1000 μF, 100 V |                     |
| R1, R12   | resistor                          | 4.7 Ω, 1 %     | SMD 0805            |
| R11       | resistor                          | 50 Ω, 25 W     | Anaren: C16A50Z4    |
| R23, R25  | resistor                          | 5.1 Ω, 1 %     | SMD 1206            |
| R24       | resistor                          | 240 Ω, 1 %     | SMD 0805            |
| CPL1      | hybrid coupler                    | 2 dB, 90°      | Anaren: X3C20F1-02S |

### 7.4 Graphical data

#### 7.4.1 Pulsed CW



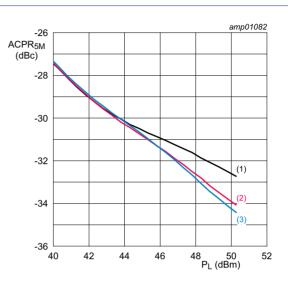
#### 7.4.2 1-Carrier W-CDMA



 $V_{DS}$  = 48 V;  $I_{Dq}$  = 400 mA;  $V_{GS(amp)peak}$  = 0.4 V.

- (1) f = 791 MHz
- (2) f = 806 MHz
- (3) f = 821 MHz

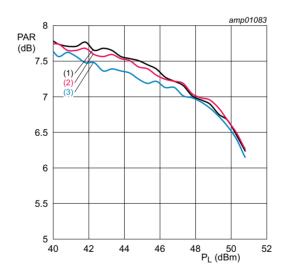
Fig 4. Power gain and drain efficiency as function of output power; typical values



 $V_{DS}$  = 48 V;  $I_{Dq}$  = 400 mA;  $V_{GS(amp)peak}$  = 0.4 V.

- (1) f = 791 MHz
- (2) f = 806 MHz
- (3) f = 821 MHz

Fig 5. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

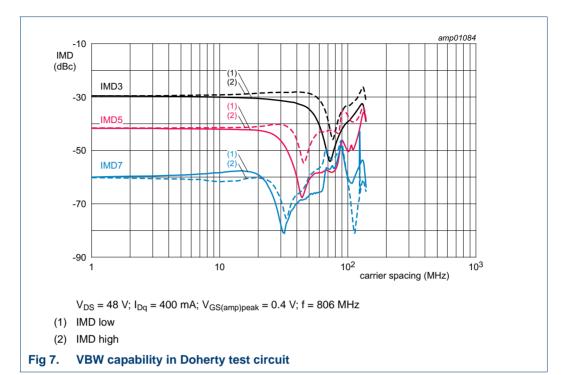


 $V_{DS}$  = 48 V;  $I_{Dq}$  = 400 mA;  $V_{GS(amp)peak}$  = 0.4 V.

- (1) f = 791 MHz
- (2) f = 806 MHz
- (3) f = 821 MHz

Fig 6. Peak-to-average power ratio as a function of output power; typical values

#### 7.4.3 2-Tone VBW



### 8. Package outline

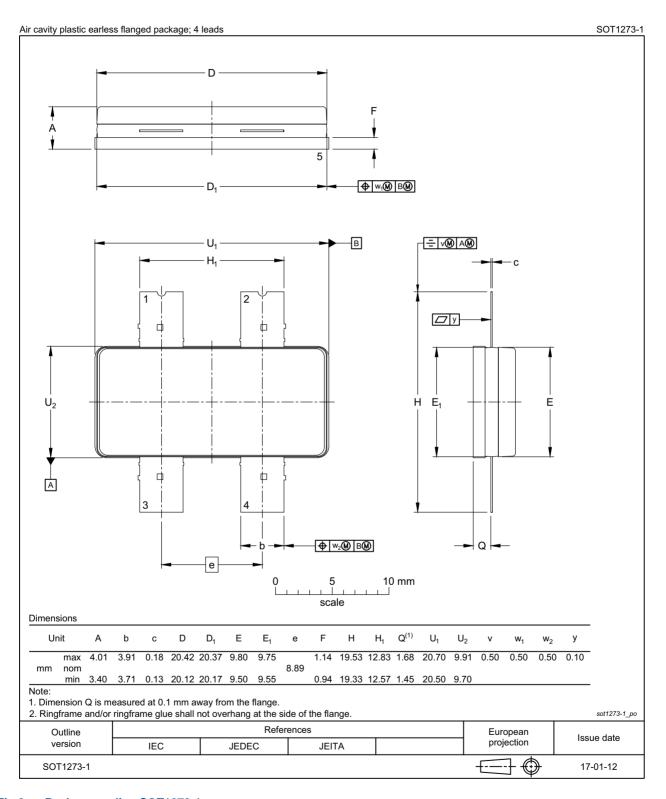


Fig 8. Package outline SOT1273-1

### 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 12. ESD sensitivity

| ESD model  | Class   |
|--|---------|
| Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002 | C2A [1] |
| Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001     | 2 [2]   |

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V.
- [2] HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V.

#### 10. Abbreviations

Table 13. Abbreviations

| Acronym | Description                                    |  |  |
|---------|--|--|--|
| 3GPP    | 3rd Generation Partnership Project             |  |  |
| CCDF    | Complementary Cumulative Distribution Function |  |  |
| CW      | Continuous Wave                                |  |  |
| DPCH    | Dedicated Physical CHannel                     |  |  |
| ESD     | ElectroStatic Discharge                        |  |  |
| LDMOS   | Laterally Diffused Metal-Oxide Semiconductor   |  |  |
| ОВО     | Output Back Off                                |  |  |
| MTF     | Median Time to Failure                         |  |  |
| PAR     | Peak-to-Average Ratio                          |  |  |
| RoHS    | Restriction of Hazardous Substances            |  |  |
| SMD     | Surface Mounted Device                         |  |  |
| VBW     | Video BandWidth                                |  |  |
| VSWR    | Voltage Standing Wave Ratio                    |  |  |
| W-CDMA  | Wideband Code Division Multiple Access         |  |  |

### 11. Revision history

Table 14. Revision history

| Document ID        | Release date | Data sheet status  | Change notice | Supersedes |
|--------------------|--------------|--------------------|---------------|------------|
| BLC9H10XS-505A v.1 | 20200306     | Product data sheet | -             | -          |

### 12. Legal information

#### 12.1 Data sheet status

| Document status[1][2]          | Product status[3] | Definition  |
|--------------------------------|-------------------|---|
| Objective [short] data sheet   | Development       | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification     | This document contains data from the preliminary specification.                       |
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#### 13. Contact information

For more information, please visit: http://www.ampleon.com

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# **BLC9H10XS-505A**

#### **Power LDMOS transistor**

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